SP1212

12A Discrete Unidirectional TVS Diode

OBSOLETE DATE: 9/30/2021 PCN/ECN# ESU270-62 REPLACED BY: SP1250-01ETG









Additional Information



Resources

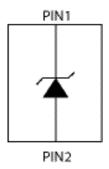




Accessories

Samples

Pinout and Functional Block Diagram



Description

The SP1212 unidirectional TVS is fabricated in a proprietary silicon avalanche technology. These diodes provide a high ESD (electrostatic discharge) protection level for electronic equipment. The SP1212 TVS can safely absorb repetitive ESD strikes of ±30 kV (contact and air discharge as defined in IEC 61000-4-2) without any performance degradation. Additionally, each TVS can safely dissipate a 12A 8/20 surge event as defined in IEC 61000-4-5 2nd Edition.

Features & Benefits

- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, 12A (8/20µs as defined in IEC 61000-4-5 2nd edition)
- AEC-Q101 qualified
- Lead free and RoHS compliant
- Moisture Sensitivity Level(MSL -1)

Applications

- Switches / Buttons
- Test Equipment / Instrumentation
- Point-of-Sale Terminals
- Medical Equipment
- Notebooks / Desktops / Servers
- Computer Peripherals
- Battery

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
P_{pk}	Peak Pulse Power (t _p =8/20μs)	250	W
T_{OP}	Operating Temperature	-40 to 125	°C
T_{stor}	Storage Temperature	-55 to 150	°C

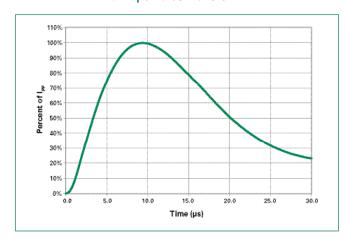
Caution: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Characteristics (T_{OP}=25°C)

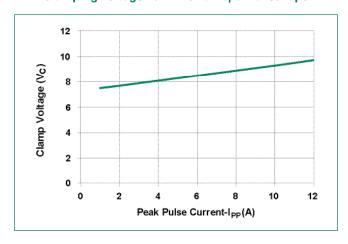
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V _{RWM}	$I_R = 1 \mu A$			5.0	V
Breakdown Voltage	V_{BR}	I _R =1mA		7.0		V
Reverse Leakage Current	I _{LEAK}	V _R =5V		0.1	0.5	μΑ
Clamp Voltage ¹	V _c	$I_{pp} = 1A$, $t_p = 8/20 \mu s$		7.5		V
		$I_{pp}=12A$, $t_{p}=8/20\mu s$		9.7		V
Dynamic Resistance ²	R _{DYN}	TLP, t_p =100ns, I/O to GND		0.33		Ω
Peak Pulse Current	l _{pp}	t _p =8/20µs		12		А
ESD Withstand Voltage ¹	V _{ESD}	IEC 61000-4-2 (Contact Discharge)	±30			kV
		IEC 61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias=0V, f=1MHz		290		pF

Note

8/20µs Pulse Waveform



Clamping Voltage vs IPP for 8/20µs waveshape

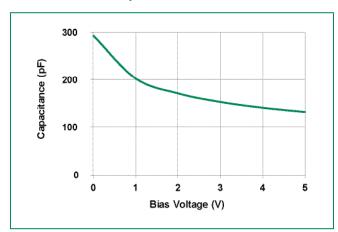


^{1.} Parameter is guaranteed by design and/or component characterization.

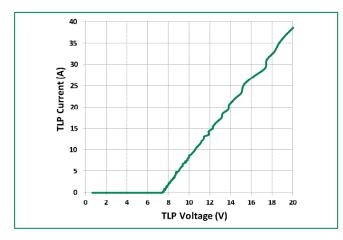
^{2.} Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window t1=70ns to t2=90ns

12A Discrete Unidirectional TVS Diode

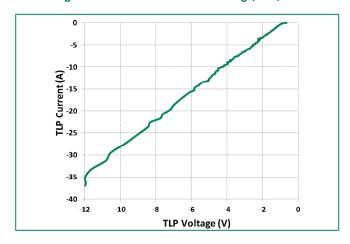
Capacitance vs. Bias



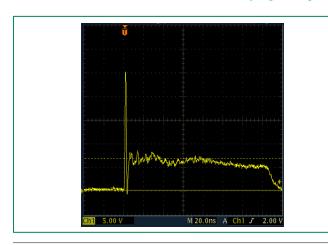
Positive Transmission Line Pulsing (TLP) Plot



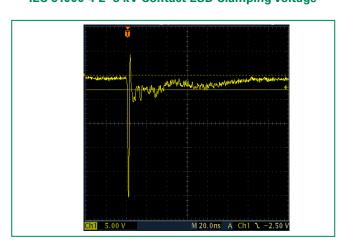
Negative Transmission Line Pulsing (TLP) Plot



IEC 61000-4-2 +8 kV Contact ESD Clamping Voltage



IEC 61000-4-2 -8 kV Contact ESD Clamping Voltage





SP1212

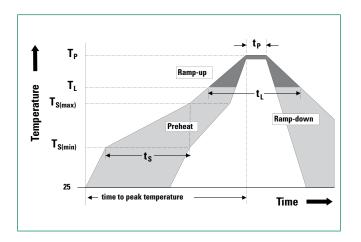
12A Discrete Unidirectional TVS Diode

Soldering Parameters

Reflow Condition		Pb – Free assembly		
Pre Heat	- Temperature Min (T _{s(min)})	150°C		
	-Temperature Max (T _{s(max)})	200°C		
	-Time (min to max) (t _s)	60 – 180 secs		
Average rar	np up rate (Liquidus) Temp (T _L)	3°C/second max		
T _{S(max)} to T _L	Ramp-up Rate	3°C/second max		
Reflow	-Temperature (T _L) (Liquidus)	217°C		
	- Temperature (t _L)	60 – 150 seconds		
Peak Tempe	erature (T _P)	260+0/-5 °C		
Time within 5°C of actual peak Temperature (t _p)		20 – 40 seconds		
Ramp-down Rate		6°C/second max		
Time 25°C to peak Temperature (T _p)		8 minutes Max.		
Do not exceed		260°C		

Ordering Information

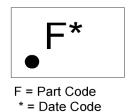
Part Number	Package	Min. Order Qty.
SP1212-01ETG	SOD882	10000



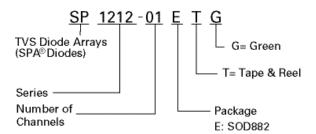
Product Characteristics

Lead Plating	Matte Tin
Lead Material	Copper Alloy
Substrate Material	Silicon
Body Material	Molded Compound
Flammability	UL Recognized compound meeting flammability rating V-0

Part Marking System



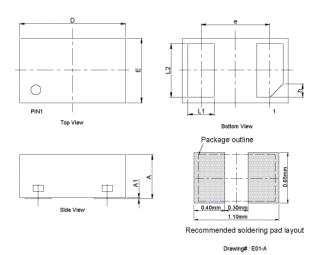
Part Numbering System



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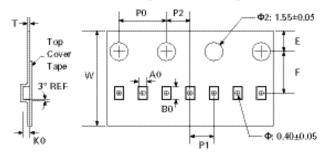
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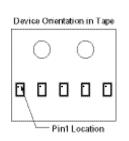
Package Dimensions — SOD882

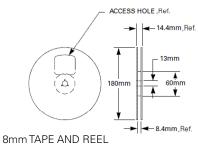


	Package	SOD882 MO-236				
Symbol	JEDEC					
Cyllibol	I	Millimeters		Inches		
	Min	Тур	Max	Min	Тур	Max
Α	0.50	0.55	0.60	0.020	0.022	0.024
A1	0.00	0.02	0.05	0.000	0.001	0.002
L1	0.20	0.25	0.30	0.008	0.010	0.012
L2	0.45	0.50	0.55	0.018	0.020	0.022
D	0.90	1.00	1.10	0.035	0.039	0.043
E	0.50	0.60	0.70	0.020	0.024	0.028
е		0.65 BSC			0.026 BSC	
h	0.	125 (x 45°	·)	0.	005 (x 45°	°)

Embossed Carrier Tape & Reel Specification — SOD882







Tape Dimensions					
Cumbal	Millimeters				
Symbol	Min	Max			
Α0	0.65	0.75			
В0	1.10	1.20			
K0	0.50	0.60			
E	1.65	1.85			
F	3.45	3.55			
P0	3.90	4.10			
P1	1.90	2.10			
P2	1.95	2.05			
Т	1.95	2.05			
w	7.90	8.10			

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